

positioning said semiconductor substrate and said sacrificial substrate holder into said plasma processing chamber;

striking said plasma from an etchant source gas released into said plasma processing chamber; and

simultaneously etching said first surface of said semiconductor substrate and said first surface of said sacrificial etch portion using said plasma.

25 [11]. (Once Amended) In a plasma processing chamber, a method for improving etch uniformity while etching a semiconductor substrate, comprising:

providing an annular sacrificial substrate holder having a planar upper surface formed of at least 99% pure aluminum;

placing a semiconductor substrate within said sacrificial substrate holder such that an upper surface of said semiconductor substrate is substantially even with said planar upper surface of said annular sacrificial substrate holder; and

creating a plasma etching cloud from an etchant source gas released into said plasma processing chamber to simultaneously etch said upper surface of said semiconductor substrate and upper planar surface of said sacrificial etch portion, wherein said sacrificial substrate holder is dimensioned such that said plasma etching cloud extends beyond an outer periphery of said sacrificial substrate holder during said etching.

REMARKS

Claims 1 and 25 have been amended to require that the sacrificial substrate holder is formed from at least 99% pure aluminum. Wicker et al. in column 6, lines 34-50, does not teach that a sacrificial substrate holder that is formed from 99% pure aluminum. Although Abraham and Abraham et al. teach the etching of an aluminum layer in a TCP™ 9600 SE plasma reactor, they do not suggest or make obvious forming the focus ring taught in Wicker et al. from 99% pure aluminum. Enclosed in US Patent No. 5,998,932 to Lenz, which describes the working and function